





Welcome to **E-XFL.COM** 

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104phafb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/G14 1. OUTLINE

#### O ROM, RAM capacities

Flash ROM Data flash		RAM	RL78/G14					
Tiasii NOW	Data ilasii	KAW	30 pins	32 pins	36 pins	40 pins		
192 KB	8 KB	20 KB	_	_	_	R5F104EH		
128 KB	8 KB	16 KB	R5F104AG	R5F104BG	R5F104CG	R5F104EG		
96 KB	8 KB	12 KB	R5F104AF	R5F104BF	R5F104CF	R5F104EF		
64 KB	4 KB	5.5 KB Note	R5F104AE	R5F104BE	R5F104CE	R5F104EE		
48 KB	4 KB	5.5 KB Note	R5F104AD	R5F104BD	R5F104CD	R5F104ED		
32 KB	4 KB	4 KB	R5F104AC	R5F104BC	R5F104CC	R5F104EC		
16 KB	4 KB	2.5 KB	R5F104AA	R5F104BA	R5F104CA	R5F104EA		

Flash ROM	Data flash	RAM	RL78/G14					
TiasiTNOW	Data ilasii	IVAIVI	44 pins	48 pins	52 pins	64 pins		
512 KB	8 KB	48 KB Note	_	R5F104GL	_	R5F104LL		
384 KB	8 KB	32 KB	_	R5F104GK	_	R5F104LK		
256 KB	8 KB	24 KB Note	R5F104FJ	R5F104GJ	R5F104JJ	R5F104LJ		
192 KB	8 KB	20 KB	R5F104FH	R5F104GH	R5F104JH	R5F104LH		
128 KB	8 KB	16 KB	R5F104FG	R5F104GG	R5F104JG	R5F104LG		
96 KB	8 KB	12 KB	R5F104FF	R5F104GF	R5F104JF	R5F104LF		
64 KB	4 KB	5.5 KB Note	R5F104FE	R5F104GE	R5F104JE	R5F104LE		
48 KB	4 KB	5.5 KB Note	R5F104FD	R5F104GD	R5F104JD	R5F104LD		
32 KB	4 KB	4 KB	R5F104FC	R5F104GC	R5F104JC	R5F104LC		
16 KB	4 KB	2.5 KB	R5F104FA	R5F104GA	_	_		

Flash ROM	Data flash	RAM	RL78/G14				
T IdSIT KOW	Data ilasii		80 pins	100 pins			
512 KB	8 KB	48 KB Note	R5F104ML	R5F104PL			
384 KB	8 KB	32 KB	R5F104MK	R5F104PK			
256 KB	8 KB	24 KB Note	R5F104MJ	R5F104PJ			
192 KB	8 KB	20 KB	R5F104MH	R5F104PH			
128 KB	8 KB	16 KB	R5F104MG	R5F104PG			
96 KB	8 KB	12 KB	R5F104MF	R5F104PF			

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H

R5F104xE (x = A to C, E to G, J, L): Start address FE900H

R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H

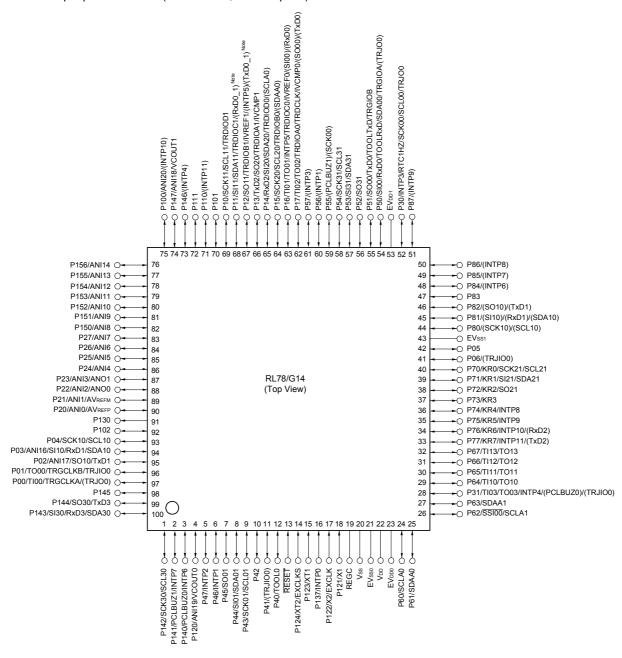
R5F104xL (x = G, L, M, P): Start address F3F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

RL78/G14 1. OUTLINE

### 1.3.10 100-pin products

• 100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)

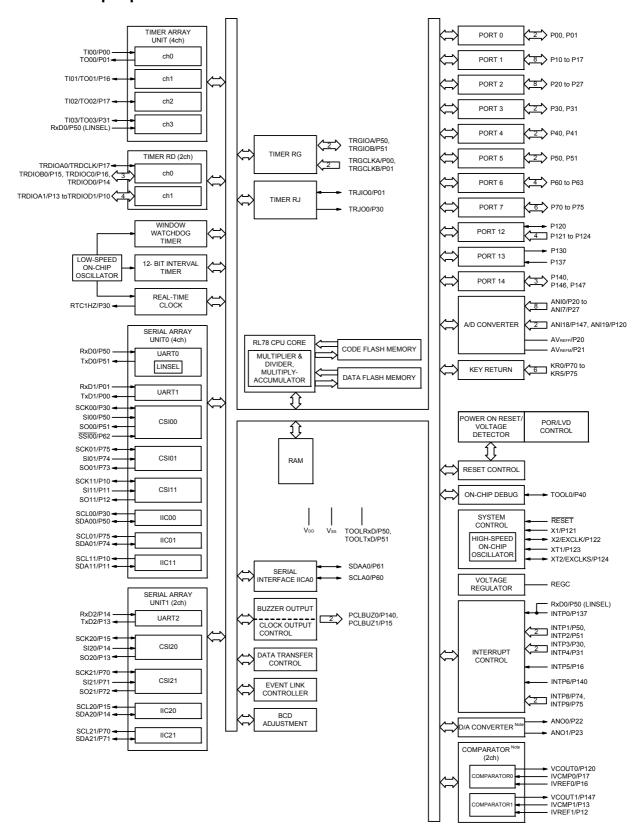


Note Mounted on the 384 KB or more code flash memory products.

- Caution 1. Make EVsso, EVss1 pins the same potential as Vss pin.
- Caution 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu\text{F}).$
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

RL78/G14 1. OUTLINE

### 1.5.6 **48-pin products**



**Note** Mounted on the 96 KB or more code flash memory products.

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	4.0 V ≤ EVDD0 ≤ 5.5 V			70.0	mA
	(When duty ≤ 70% Note 3)		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V			15.0	mA
		1.8 V ≤ EV <sub>DD0</sub> < 2.7 V			9.0	mA	
			1.6 V ≤ EVDD0 < 1.8 V			4.5	mA
		Total of P05, P06, P10 to P17,	4.0 V ≤ EVDD0 ≤ 5.5 V			80.0	mA
		P30, P31, P50 to P57,	2.7 V ≤ EVDD0 < 4.0 V			35.0	mA
		P60 to P67, P70 to P77, P80 to P87, P100, P101, P110,	1.8 V ≤ EVDD0 < 2.7 V			20.0	mA
		P111, P146, P147 (When duty ≤ 70% Note 3)	1.6 V ≤ EVDD0 < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )				150.0	mA
	lol2	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )	1.6 V ≤ VDD ≤ 5.5 V			5.0	mA

- **Note 1.** Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1, and Vss pins.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoL × 0.7)/(n × 0.01)

<Example> Where n = 80% and lol = 10.0 mA

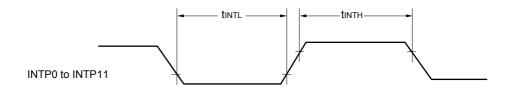
Total output current of pins =  $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$ 

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

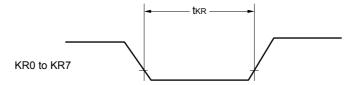
A current higher than the absolute maximum rating must not flow into one pin.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

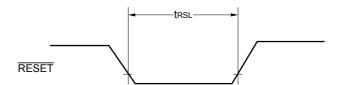
### Interrupt Request Input Timing



## Key Interrupt Input Timing



## RESET Input Timing

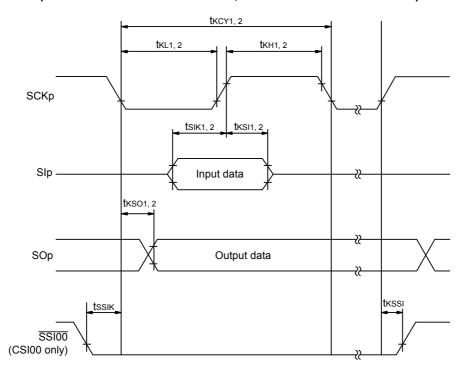


## (3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

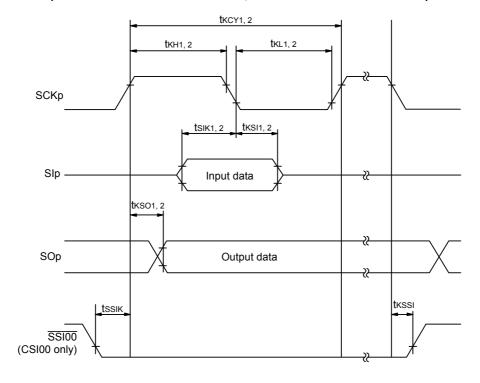
Parameter	Symbol	Conditions		HS (high-s main) mo		LS (low-speed mode	d main)	LV (low-vol	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	2.7 V ≤ EVDD0 ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	_		1000		1000		ns
SCKp high-/low-level	tĸнı,	4.0 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 12		tkcy1/2 - 50		tkcy1/2 - 50		ns
width	tKL1	2.7 V ≤ EVDD0 ≤ 5.5 V		tkcy1/2 - 18		tkcy1/2 - 50		tkcy1/2 - 50		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		tkcy1/2 - 38		tkcy1/2 - 50		tkcy1/2 - 50		ns
		1.8 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 50		tkcy1/2 - 50		tkcy1/2 - 50		ns
		1.7 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 100		tkcy1/2 - 100		tkcy1/2 - 100		ns
		1.6 V ≤ EVDD0	≤ 5.5 V	_		tkcy1/2 - 100		tkcy1/2 - 100		ns
SIp setup time	tsıĸ1	4.0 V ≤ EVDD0 ≤ 5.5 V		44		110		110		ns
(to SCKp↑) Note 1		2.7 V ≤ EVDD0 ≤ 5.5 V		44		110		110		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		75		110		110		ns
		1.8 V ≤ EVDD0	≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EVDD0	≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EVDD0	≤ 5.5 V	_		220		220		ns
SIp hold time	tksi1	1.7 V ≤ EVDD0	≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EVDD0	≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	1.7 V ≤ EV <sub>DD0</sub> C = 30 pF Note			25		25		25	ns
Note 3		1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V C = 30 pF Note 4			_		25		25	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)
- Remark 2. fmck: Serial array unit operation clock frequency
  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

# CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



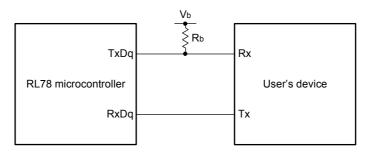
# CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



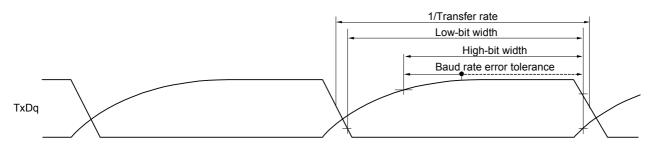
**Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

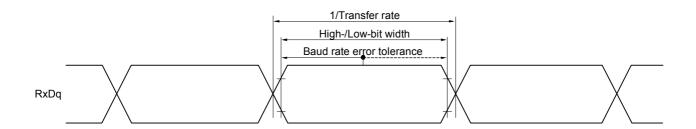
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

#### **UART** mode connection diagram (during communication at different potential)



#### UART mode bit width (during communication at different potential) (reference)





- Remark 1.  $Rb[\Omega]$ : Communication line (TxDq) pull-up resistance,
  - Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency
  - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
  - m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
- Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is

# (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(TA = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	ol Conditions			h-speed mode		r-speed mode		-voltage mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY2	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	24 MHz < fmck	14/fмск		_		_		ns
Note 1		$2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	12/fмск		_		_		ns
			8 MHz < fмcк ≤ 20 MHz	10/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$	24 MHz < fmck	20/fмск		_		_		ns
		$2.3~V \leq V_b \leq 2.7~V$	20 MHz < fмcк ≤ 24 MHz	16/fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		1.8 V ≤ EVDD0 < 3.3 V,	24 MHz < fmck	48/fмск		_		_		ns
	$1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$ Note 2	20 MHz < fмcк ≤ 24 MHz	36/fмск		_		_		ns	
		Note 2	16 MHz < fмcк ≤ 20 MHz	32/fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	26/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	10/fмск		10/fмск		10/fмск		ns
SCKp high-/ low-level width	tĸH2, tĸL2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	tксү2/2 - 12		tkcy2/2 - 50		tксү2/2 - 50		ns	
		2.7 V ≤ EVDD0 < 4.0 V, 2	$2.3~V \leq V_b \leq 2.7~V$	tксү2/2 - 18		tkcy2/2 - 50		tксү2/2 - 50		ns
		1.8 V ≤ EVDD0 < 3.3 V,	tксү2/2 - 50		tkcy2/2 - 50		tксү2/2 - 50		ns	
SIp setup time (to SCKp↑) Note 3	tsık2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns	
		1.8 V ≤ EVDD0 < 3.3 V,	$1.6~\text{V} \leq \text{V}_\text{b} \leq 2.0~\text{V}~\text{Note}~2$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp↑) Note 4	tksi2			1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp	tkso2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, \Omega$ Cb = 30 pF, Rb = 1.4 k $\Omega$			2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
output Note 5		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \Omega$ Cb = 30 pF, Rb = 2.7 k $\Omega$			2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, C <sub>b</sub> = 30 pF, Rv = 5.5 kΩ	$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V} \text{ Note 2},$		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

 $(\textbf{Notes},\,\textbf{Caution},\, \text{and}\,\, \textbf{Remarks}$  are listed on the next page.)

Operation of products rated "G: Industrial applications ( $TA = -40 \text{ to} + 105^{\circ}\text{C}$ )" at ambient operating temperatures above 85°C differs from that of products rated "A: Consumer applications" and "D: Industrial applications" in the ways listed below.

Parameter	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	TA = -40 to +105°C
Operating mode	HS (high-speed main) mode:	HS (high-speed main) mode only:
Operating voltage range	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V@1 MHz to 32 MHz	2.7 V ≤ VDD ≤ 5.5 V@1 MHz to 32 MHz
	2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V@1 MHz to 16 MHz	2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V@1 MHz to 16 MHz
	LS (low-speed main) mode:	
	1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V <b>@</b> 1 MHz to 8 MHz	
	LV (low-voltage main) mode:	
	1.6 V ≤ VDD ≤ 5.5 V@1 MHz to 4 MHz	
High-speed on-chip oscillator	1.8 V ≤ VDD ≤ 5.5 V:	2.4 V ≤ VDD ≤ 5.5 V:
clock accuracy	±1.0% @ TA = -20 to +85°C	±2.0% @ TA = +85 to +105°C
	±1.5% @ TA = -40 to -20°C	±1.0% @ TA = -20 to +85°C
	1.6 V ≤ V <sub>DD</sub> < 1.8 V:	±1.5% @ TA = -40 to -20°C
	±5.0% @ TA = -20 to +85°C	
	±5.5% @ TA = -40 to -20°C	
Serial array unit	UART	UART
	CSI: fclk/2 (16 Mbps supported), fclk/4	CSI: fclk/4
	Simplified I <sup>2</sup> C communication	Simplified I <sup>2</sup> C communication
IICA	Standard mode	Standard mode
	Fast mode	Fast mode
	Fast mode plus	
Voltage detector	• Rising: 1.67 V to 4.06 V (14 stages)	• Rising: 2.61 V to 4.06 V (8 stages)
	• Falling: 1.63 V to 3.98 V (14 stages)	• Falling: 2.55 V to 3.98 V (8 stages)

Remark The electrical characteristics of products rated "G: Industrial applications (TA = -40 to + 105°C)" at ambient operating temperatures above 85°C differ from those of products rated "A: Consumer applications" and "D: Industrial applications". For details, refer to **3.1** to **3.10**.

### (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = 0 V)(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	( ) ,		fhoco = 64 MHz,	V <sub>DD</sub> = 5.0 V		0.80	4.36	mA
Note 1	Note 2		mode Note 7	fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.80	4.36	
				fhoco = 32 MHz,	V <sub>DD</sub> = 5.0 V		0.49	3.67	
				fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.49	3.67	
				fносо = 48 MHz,	V <sub>DD</sub> = 5.0 V		0.62	3.42	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.62	3.42	
				fHOCO = 24 MHz,	V <sub>DD</sub> = 5.0 V		0.4	2.85	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.4	2.85	
				fHOCO = 16 MHz,	V <sub>DD</sub> = 5.0 V		0.37	2.08	
			fih = 16 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.37	2.08		
			HS (high-speed main) mode Note 7	f <sub>MX</sub> = 20 MHz Note 3,	Square wave input		0.28	2.45	mA
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.40	2.57	
			fmx = 20 MHz Note 3,	Square wave input		0.28	2.45		
			V <sub>DD</sub> = 3.0 V	Resonator connection		0.40	2.57		
			fmx = 10 MHz Note 3,	Square wave input		0.19	1.28		
			V <sub>DD</sub> = 5.0 V	Resonator connection		0.25	1.36		
	f <sub>MX</sub> = 10 MHz Note 3, V <sub>DD</sub> = 3.0 V	fmx = 10 MHz Note 3,	Square wave input		0.19	1.28			
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.25	1.36	
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μА
			operation	TA = -40°C	Resonator connection		0.44	0.76	
			fsuB = 32.768 kHz Note 5,	Square wave input		0.30	0.57		
				TA = +25°C	Resonator connection		0.49	0.76	1
				fsuB = 32.768 kHz Note 5,	Square wave input		0.36	1.17	
				TA = +50°C	Resonator connection		0.59	1.36	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				T <sub>A</sub> = +70°C	Resonator connection		0.72	2.16	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				TA = +85°C	Resonator connection		1.16	3.56	
				fsuB = 32.768 kHz Note 5,	Square wave input		3.20	17.10	
				T <sub>A</sub> = +105°C	Resonator connection		3.40	17.50	
	IDD3 STOP mode	T <sub>A</sub> = -40°C					0.51	μΑ	
Note 6 Note	Note 8	T <sub>A</sub> = +25°C				0.24	0.51		
		T <sub>A</sub> = +50°C	T <sub>A</sub> = +50°C			0.29	1.10		
			T <sub>A</sub> = +70°C				0.41	1.90	
			T <sub>A</sub> = +85°C					3.30	1
			T <sub>A</sub> = +105°C				3.10	17.00	

(Notes and Remarks are listed on the next page.)

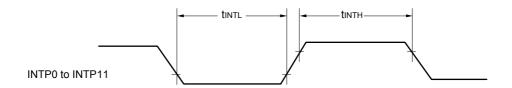
- Note 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- **Note 7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz to } 32 \text{ MHz}$ 

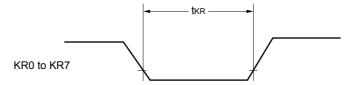
 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz to } 16 \text{ MHz}$ 

- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

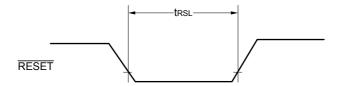
### Interrupt Request Input Timing



## Key Interrupt Input Timing

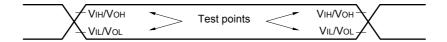


## RESET Input Timing



## 3.5 Peripheral Functions Characteristics

**AC Timing Test Points** 



### 3.5.1 Serial array unit

#### (1) During communication at same potential (UART mode)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ EVDD0 ≤ 5.5 V		fMCK/12 Note 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \le \text{EV}_{DD0} < 2.7 \text{ V: MAX. } 1.3 \text{ Mbps}$ 

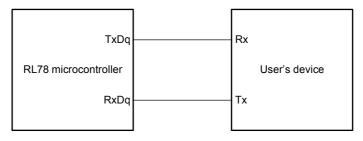
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V  $\leq$  VDD  $\leq$  5.5 V)

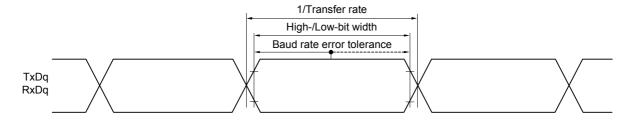
16 MHz (2.4 V  $\leq$  VDD  $\leq$  5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

#### **UART** mode connection diagram (during communication at same potential)



#### UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 2. fmck: Serial array unit operation clock frequency

 $(Operation\ clock\ to\ be\ set\ by\ the\ CKSmn\ bit\ of\ serial\ mode\ register\ mn\ (SMRmn).\ m:\ Unit\ number,$ 

n: Channel number (mn = 00 to 03, 10 to 13))

## (3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

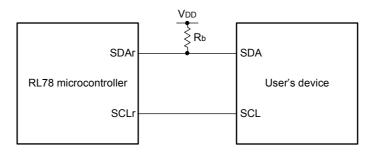
Parameter	Symbol	Cond	ditions	HS (high-speed	main) mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 5	tkcy2	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	20 MHz < fmck	16/ƒмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	fмcк ≤ 16 MHz			ns
						ns
		2.4 V ≤ EVDD0 ≤ 5.5 V				ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V			ns
		2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		tkcy2/2 - 16		ns
		2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		tkcy2/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	tsık2	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		1/fмск + 40		ns
		2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 2	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	C = 30 pF Note 4	2.7 V ≤ EVDD0 ≤ 5.5 V		2/fмск + 66	ns
			2.4 V ≤ EVDD0 ≤ 5.5 V		2/fмск + 113	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- **Note 5.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)
- Remark 2. fMCK: Serial array unit operation clock frequency

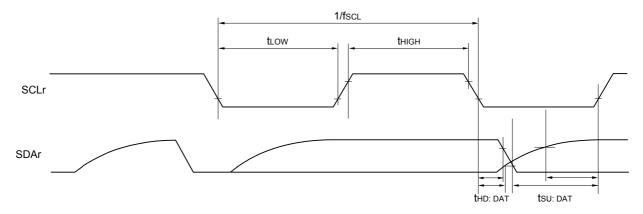
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

#### Simplified I<sup>2</sup>C mode connection diagram (during communication at same potential)



#### Simplified I<sup>2</sup>C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \ R_b[\Omega]: \ Communication \ line \ (SDAr) \ pull-up \ resistance, \ C_b[F]: \ Communication \ line \ (SDAr, SCLr) \ load \ capacitance$ 

**Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 3 to 5, 14), h: POM number (h = 0, 1, 3 to 5, 7, 14)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

## (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$ 

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note	tsıĸ1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega $	162		ns
		$\begin{aligned} 2.7 & \ V \le EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	354		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$	958		ns
SIp hold time (from SCKp↑) Note	tksıı	$ 4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b = 30 \text{ pF}, \text{Rb} = 1.4 \text{ k}\Omega $	38		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	38		ns
Delay time from SCKp↓ to SOp output Note	tkso1	$ 4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ k}\Omega $		200	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		390	ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

### (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-spe	Unit	
			MIN.	MAX.	
SCLr clock frequency	fscL	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $		400 Note 1	kHz
		$\begin{split} 2.7 & \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega \end{split}$		400 Note 1	kHz
		$\begin{aligned} 4.0 & \text{V} \leq \text{EVDD0} \leq 5.5 \text{ V}, \\ 2.7 & \text{V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b = 100 \text{ pF, } R_b = 2.8 \text{ k}\Omega \end{aligned}$		100 Note 1	kHz
		$\begin{split} 2.7 & \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{split}$		100 Note 1	kHz
		$ 2.4 \text{ V} \leq \text{EVDDO} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}, \\ C_b = 100 \text{ pF, } R_b = 5.5 \text{ k}\Omega $		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$ 4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b = 50 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega $	1200		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1200		ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	4600		ns
		$\begin{split} 2.7 & \text{ V} \leq \text{EVDD0} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 100 \text{ pF, } R_b = 2.7 \text{ k}\Omega \end{split}$	4600		ns
		$\begin{aligned} 2.4 & \text{ V} \leq \text{EVDDO} < 3.3 \text{ V}, \\ 1.6 & \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}, \\ C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega \end{aligned}$	4650		ns
Hold time when SCLr = "H"	thigh	$ \begin{aligned} 4.0 \ V &\leq EV_{DDO} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	620		ns
		$\begin{split} 2.7 & \ V \le EV_{DDO} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 50 & \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	500		ns
		$\begin{aligned} 4.0 & \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b &= 100 \text{ pF, Rb} = 2.8 \text{ k}\Omega \end{aligned}$	2700		ns
		$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 100 \ pF, \ R_{b} = 2.7 \ k \Omega \end{split}$	2400		ns
		$\begin{array}{c} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	1830		ns

R5F104LCAFB, R5F104LDAFB, R5F104LEAFB, R5F104LFAFB, R5F104LGAFB, R5F104LHAFB, R5F104LJAFB

R5F104LCDFB, R5F104LDDFB, R5F104LEDFB, R5F104LFDFB, R5F104LGDFB, R5F104LHDFB, R5F104LJDFB

R5F104LCGFB, R5F104LDGFB, R5F104LEGFB, R5F104LFGFB, R5F104LGGFB, R5F104LHGFB, R5F104LJGFB

	JEITA Package Code	RENESAS Code	Previous Cod	е	MAS	S (TYP.)	[g]
	P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UE	J-2		0.35	
	HD————————————————————————————————————	33 32	+		$\theta$	etail of	(UNIT:mm)
	64	17	$\Rightarrow$		-	ITEM D	10.00±0.20
	1	16	1		-	Е	10.00±0.20
	<del>  `                                    </del>		1		-	HD	12.00±0.20
ZE			<b>↓</b>		-	HE	12.00±0.20
					-	Α	1.60 MAX.
-	<mark>- ZD</mark>	→ e			-	A1	0.10±0.05
					-	A2	1.40±0.05
		x M S			-	A3	0.25
				Α	-	b	0.22±0.05
			<b>A2</b> ¬		-	С	0.145 +0.055 -0.045
					-	L	0.50
					_	Lp	0.60±0.15
$\Gamma$	<del>;                                    </del>	тининн —	\		S	L1	1.00±0.20
	<del></del>			•		θ	3°+5° -3°
	□ y S		A1		-	е	0.50
			, , ,			x	0.08

©2012 Renesas Electronics Corporation. All rights reserved.

0.08

1.25

1.25

ZD

ZE

NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

ZE

REVISION HISTORY	RL78/G14 Datasheet
------------------	--------------------

Rev. Date		Description		
Rev. Date	Page	Summary		
3.20	Jan 05, 2015	p.135, 137, 139, 141, 143, 145	Modification of specifications in 3.3.2 Supply current characteristics	
		p.197	Modification of part number in 4.7 52-pin products	
3.30	Aug 12, 2016	p.143, 145	Addition of maximum values in (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products of 3.3.2 Supply current characteristics	

SuperFlash is a registered trademark of Silicon Storage Technology, Inc. in several countries including the United States and Japan.

Caution: This product uses SuperFlash® technology licensed from Silicon Storage Technology, Inc.

All trademarks and registered trademarks are the property of their respective owners.